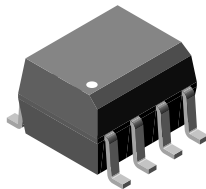


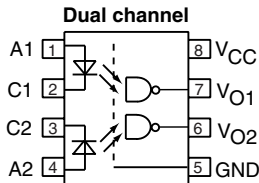
## High Speed Optocoupler, 10 MBd, SOIC-8 Package



20050



18921-16



SFH6755T/56T/57T

### FEATURES

- Choice of CMR performance of 15 kV/μs, 5 kV/μs, and 100 V/μs
- External creepage distance > 5 mm
- High speed: 10 Mbd typical
- + 5 V CMOS compatibility
- Guaranteed AC and DC performance over temperature: - 40 °C to + 100 °C temperature range
- Pure tin leads
- Meets IEC 60068-2-42 (SO<sub>2</sub>) and IEC 60068-2-43 (H<sub>2</sub>S) requirements
- Low input current capability: 5 mA
- Lead (Pb)-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



**RoHS**  
COMPLIANT

### DESCRIPTION

The SFH675xT-series, is a dual channel 10 MBd optocoupler utilizing a high efficient input LED coupled with an integrated optical photodiode IC detector. The detector has an open drain NMOS-transistor output, providing less leakage compared to an open collector Schottky clamped transistor output. The internal shield provides a guaranteed common mode transient immunity of 5 kV/μs for the SFH6756T and 15 kV/μs for the SFH6757T. The use of a 0.1 μF bypass capacitor connected between pin 5 and 8 is recommended.

### AGENCY APPROVALS

- UL1577, file no. E52744 system code Y
- CUL - file no. E52744, equivalent to CSA bulletin 5A
- DIN EN 60747-5-5 (VDE 0884) available with option 1

### APPLICATIONS

- Microprocessor system interface
- PLC, ATE input/output isolation
- Computer peripheral interface
- Digital fieldbus isolation: CC-link, DeviceNet, profibus, SDS
- High speed A/D and D/A conversion
- AC plasma display panel level shifting
- Multiplexed data transmission
- Digital control power supply
- Ground loop elimination

### ORDER INFORMATION

PART	REMARKS
SFH6755T	100 V/μs, dual channel, SOIC-8
SFH6756T	5 kV/μs, dual channel, SOIC-8
SFH6757T	15 kV/μs, dual channel, SOIC-8

### TRUTH TABLE (positive logic)

LED	ENABLE	OUTPUT
ON	H	L
OFF	H	H
ON	L	H
OFF	L	H
ON	NC	L
OFF	NC	H

# SFH6755T, SFH6756T, SFH6757T



Vishay Semiconductors High Speed Optocoupler, 10 MBd,  
SOIC-8 Package

ABSOLUTE MAXIMUM RATINGS (1)				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
<b>INPUT</b>				
Average forward current (single channel)		$I_F$	20	mA
Average forward current (per channel for dual channel)		$I_F$	15	mA
Reverse input voltage		$V_R$	5	V
Surge current	$t = 100 \mu\text{s}$	$I_{FSM}$	200	mA
Output power dissipation (single channel)		$P_{diss}$	35	mW
Output power dissipation (per channel for dual channel)		$P_{diss}$	25	mW
<b>OUTPUT</b>				
Supply voltage	1 min maximum	$V_{CC}$	7	V
Output current		$I_O$	50	mA
Output voltage		$V_O$	7	V
Output power dissipation (single channel)		$P_{diss}$	85	mW
Output power dissipation (for dual channel)		$P_{diss}$	60	mW
<b>COUPLER</b>				
Isolation test voltage	$t = 1.0 \text{ s}$	$V_{ISO}$	4000	$V_{RMS}$
Storage temperature		$T_{stg}$	- 55 to + 150	$^{\circ}\text{C}$
Operating temperature		$T_{amb}$	- 40 to + 100	$^{\circ}\text{C}$
Lead solder temperature	for 10 s		260	$^{\circ}\text{C}$
Solder reflow temperature (2)	for 1 min	$T_{sld}$	260	$^{\circ}\text{C}$

## Notes

(1)  $T_{amb} = 25 \text{ }^{\circ}\text{C}$ , unless otherwise specified.

Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute maximum ratings for extended periods of the time can adversely affect reliability.

(2) Refer to reflow profile for soldering conditions for surface mounted devices.

RECOMMENDED OPERATING CONDITIONS					
PARAMETER	TEST CONDITION	SYMBOL	MIN.	MAX.	UNIT
Operating temperature		$T_{amb}$	- 40	100	$^{\circ}\text{C}$
Supply voltage		$V_{CC}$	4.5	5.5	V
Input current low level		$I_{FL}$	0	250	$\mu\text{A}$
Input current high level		$I_{FH}$	5	15	mA
Output pull up resistor		$R_L$	330	4K	$\Omega$
Fanout	$R_L = 1 \text{ k}\Omega$	N		5	-

THERMAL CHARACTERISTICS					
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT	
LED power dissipation	at 25 $^{\circ}\text{C}$	$P_{diss}$	100	mW	
Output power dissipation	at 25 $^{\circ}\text{C}$	$P_{diss}$	500	mW	
Maximum LED junction temperature		$T_{jmax}$	125	$^{\circ}\text{C}$	
Maximum output die junction temperature		$T_{jmax}$	125	$^{\circ}\text{C}$	
Thermal resistance, junction emitter to emitter		$\theta_{EE}$	412	$^{\circ}\text{C}/\text{W}$	
Thermal resistance, junction detector to emitter		$\theta_{DE}$	133	$^{\circ}\text{C}/\text{W}$	



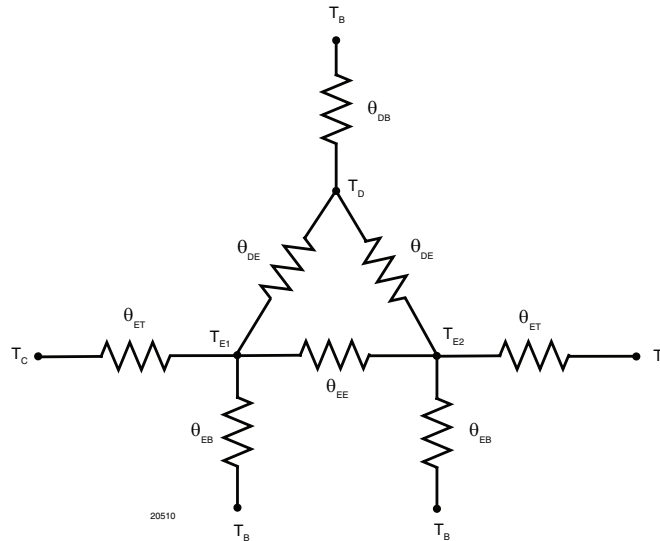
# SFH6755T, SFH6756T, SFH6757T

High Speed Optocoupler, 10 MBd, Vishay Semiconductors  
SOIC-8 Package

THERMAL CHARACTERISTICS				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Thermal resistance, junction emitter to board		$\theta_{EB}$	120	$^{\circ}\text{C}/\text{W}$
Thermal resistance, junction detector to board		$\theta_{DB}$	77	$^{\circ}\text{C}/\text{W}$
Thermal resistance, junction emitter to case		$\theta_{EC}$	110	$^{\circ}\text{C}/\text{W}$

### Note

The thermal model is represented in the thermal network below. Each resistance value given in this model can be used to calculate the temperatures at each node for a given operating condition. The thermal resistance from board to ambient will be dependent on the type of PCB, layout and thickness of copper traces. For a detailed explanation of the thermal model, please reference Vishay's Thermal Characteristics of Optocouplers Application note.



ELECTRICAL CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
<b>INPUT</b>						
Input forward voltage	$I_F = 10 \text{ mA}$	$V_F$	1.1	1.4	1.7	V
Reverse current	$V_R = 5 \text{ V}$	$I_R$		0.01	10	$\mu\text{A}$
Input capacitance	$f = 1 \text{ MHz}, V_F = 0 \text{ V}$	$C_I$		55		pF
<b>OUTPUT</b>						
High level supply current (single channel)	$V_E = 0.5 \text{ V}, I_F = 0 \text{ mA}$	$I_{CCH}$		4.1	7.0	mA
	$V_E = V_{CC}, I_F = 0 \text{ mA}$	$I_{CCH}$		3.3	6.0	mA
High level supply current (dual channel)	$I_F = 0 \text{ mA}$	$I_{CCH}$		6.5	12.0	mA
Low level supply current (single channel)	$V_E = 0.5 \text{ V}, I_F = 10 \text{ mA}$	$I_{CCL}$		4.0	7.0	mA
	$V_E = V_{CC}, I_F = 10 \text{ mA}$	$I_{CCL}$		3.3	6.0	mA
Low level supply current (dual channel)	$I_F = 10 \text{ mA}$	$I_{CCL}$		6.5	12.0	mA
High level output current	$V_E = 2 \text{ V}, V_O = 5.5 \text{ V}, I_F = 250 \mu\text{A}$	$I_{OH}$		0.002	1	$\mu\text{A}$
Low level output voltage	$V_E = 2 \text{ V}, I_F = 5 \text{ mA}, I_{OL} \text{ (sinking)} = 13 \text{ mA}$	$V_{OL}$		0.2	0.6	V
Input threshold current	$V_E = 2 \text{ V}, V_O = 5.5 \text{ V}, I_{OL} \text{ (sinking)} = 13 \text{ mA}$	$I_{TH}$		2.4	5.0	mA

### Note

$T_{amb} = 25 \text{ }^{\circ}\text{C}$ , and  $V_{CC} = 5.5 \text{ V}$ , unless otherwise specified.

Minimum and maximum values are testing requirements. Typical values are characteristics of the device and are the result of engineering evaluation. Typical values are for information only and are not part of the testing requirements.

SWITCHING CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Propagation delay time to high output level	$R_L = 350 \Omega, C_L = 15 \text{ pF}$	$t_{PLH}$	20	48	100	ns
Propagation delay time to low output level	$R_L = 350 \Omega, C_L = 15 \text{ pF}$	$t_{PHL}$	25	50	100	ns
Pulse width distortion	$R_L = 350 \Omega, C_L = 15 \text{ pF}$	$ t_{PHL} - t_{PLH} $		2.9	35	ns
Propagation delay skew	$R_L = 350 \Omega, C_L = 15 \text{ pF}$	$t_{PSK}$		8	40	ns
Output rise time (10 to 90 %)	$R_L = 350 \Omega, C_L = 15 \text{ pF}$	$t_r$		23		ns
Output fall time (90 to 10 %)	$R_L = 350 \Omega, C_L = 15 \text{ pF}$	$t_f$		7		ns

**Note**

Over recommended temperature ( $T_A = -40 \text{ }^\circ\text{C}$  to  $+100 \text{ }^\circ\text{C}$ ),  $V_{CC} = 5 \text{ V}$ ,  $I_F = 7.5 \text{ mA}$  unless otherwise specified.  
All typicals at  $T_{amb} = 25 \text{ }^\circ\text{C}$ ,  $V_{CC} = 5 \text{ V}$ .

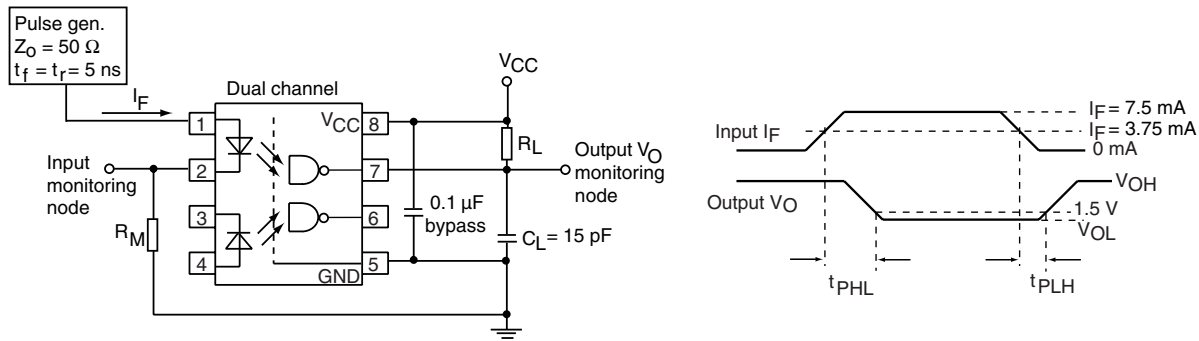


Fig. 1 - Dual Channel Test Circuit for  $t_{PLH}$ ,  $t_{PHL}$ ,  $t_r$  and  $t_f$

COMMON MODE TRANSIENT IMMUNITY						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Common mode transient immunity (high)	$ V_{CM}  = 10 \text{ V}, V_{CC} = 5 \text{ V}, I_F = 0 \text{ mA}, V_{O(min.)} = 2 \text{ V}, R_L = 350 \Omega, T_{amb} = 25 \text{ }^\circ\text{C}$ (1)	$ CM_H $	100			$\text{V}/\mu\text{s}$
	$ V_{CM}  = 50 \text{ V}, V_{CC} = 5 \text{ V}, I_F = 0 \text{ mA}, V_{O(min.)} = 2 \text{ V}, R_L = 350 \Omega, T_{amb} = 25 \text{ }^\circ\text{C}$ (2)	$ CM_H $	5000	10 000		$\text{V}/\mu\text{s}$
	$ V_{CM}  = 1 \text{ kV}, V_{CC} = 5 \text{ V}, I_F = 0 \text{ mA}, V_{O(min.)} = 2 \text{ V}, R_L = 350 \Omega, T_{amb} = 25 \text{ }^\circ\text{C}$ (3)	$ CM_H $	15 000	25 000		$\text{V}/\mu\text{s}$
Common mode transient immunity (low)	$ V_{CM}  = 10 \text{ V}, V_{CC} = 5 \text{ V}, I_F = 7.5 \text{ mA}, V_{O(max.)} = 0.8 \text{ V}, R_L = 350 \Omega, T_{amb} = 25 \text{ }^\circ\text{C}$ (1)	$ CM_L $	100			$\text{V}/\mu\text{s}$
	$ V_{CM}  = 50 \text{ V}, V_{CC} = 5 \text{ V}, I_F = 7.5 \text{ mA}, V_{O(max.)} = 0.8 \text{ V}, R_L = 350 \Omega, T_{amb} = 25 \text{ }^\circ\text{C}$ (2)	$ CM_L $	5000	10 000		$\text{V}/\mu\text{s}$
	$ V_{CM}  = 1 \text{ kV}, V_{CC} = 5 \text{ V}, I_F = 7.5 \text{ mA}, V_{O(max.)} = 0.8 \text{ V}, R_L = 350 \Omega, T_{amb} = 25 \text{ }^\circ\text{C}$ (3)	$ CM_L $	15 000	25 000		$\text{V}/\mu\text{s}$

**Notes**

- (1) For SFH6755T
- (2) For SFH6756T
- (3) For SFH6757T

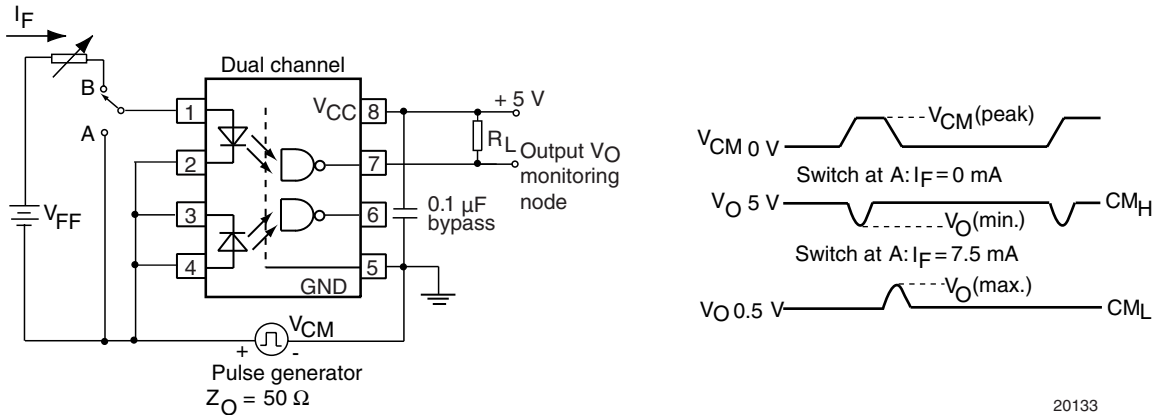


Fig. 2 - Dual Channel Test Circuit for Common Mode Transient Immunity

SAFETY AND INSULATION RATINGS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Climatic classification (according to IEC 68 part 1)				55/100/21		
Comparative tracking index		CTI	175		399	
Peak transient overvoltage		$V_{IOTM}$	6000			V
Peak insulation voltage		$V_{IORM}$	560			V
Safety rating - power output		$P_{SO}$			350	mW
Safety rating - input current		$I_{SI}$			150	mA
Safety rating - temperature		$T_{SI}$			165	°C
Creepage distance			5			mm
Clearance distance			4			mm
Insulation thickness			0.2			mm

**Note**

As per IEC 60747-5-2, §7.4.3.8.1, this optocoupler is suitable for “safe electrical insulation” only within the safety ratings. Compliance with the safety ratings shall be ensured by means of protective circuits.

**TYPICAL CHARACTERISTICS**

$T_{amb} = 25\text{ °C}$ , unless otherwise specified

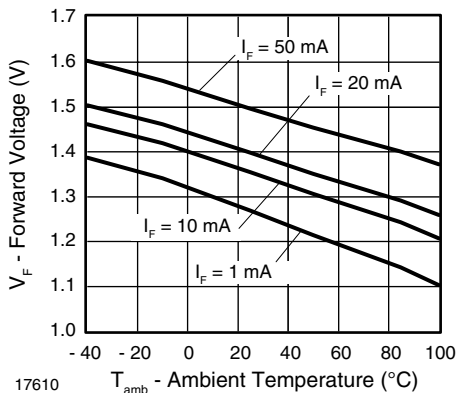


Fig. 3 - Forward Voltage vs. Ambient Temperature

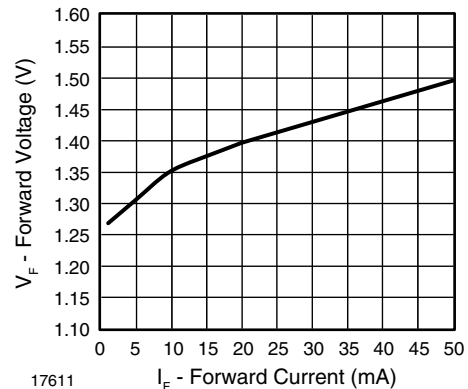


Fig. 4 - Forward Voltage vs. Forward Current

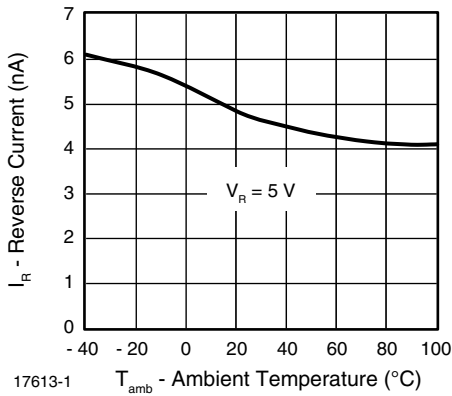


Fig. 5 - Reverse Current vs. Ambient Temperature

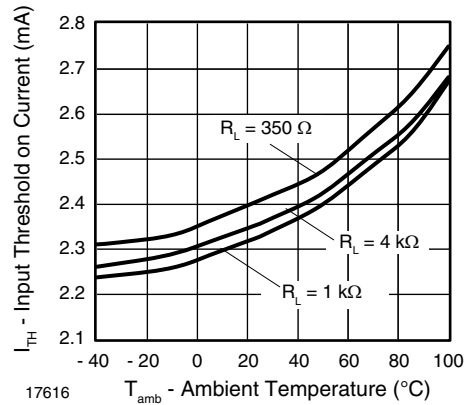


Fig. 8 - Input Threshold on Current vs. Ambient Temperature

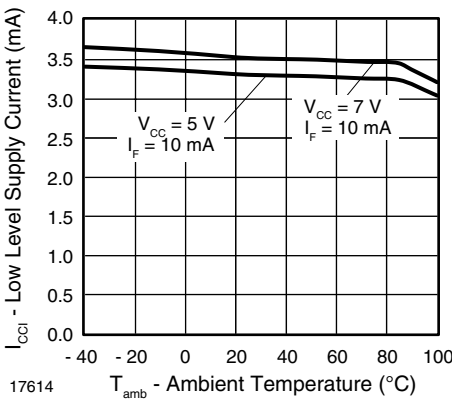


Fig. 6 - Low Level Supply Current vs. Ambient Temperature

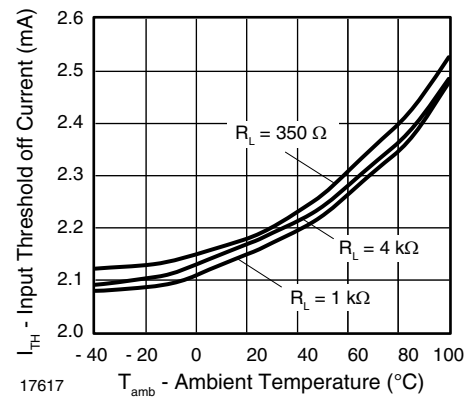


Fig. 9 - Input Threshold off Current vs. Ambient Temperature

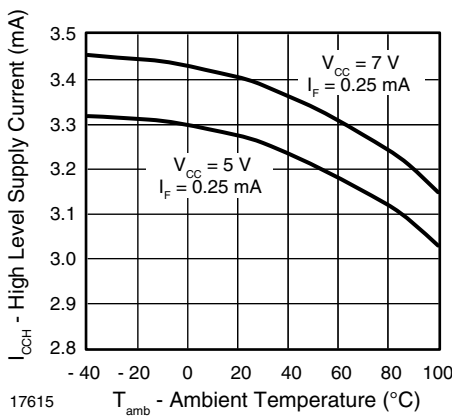


Fig. 7 - High Level Supply Current vs. Ambient Temperature

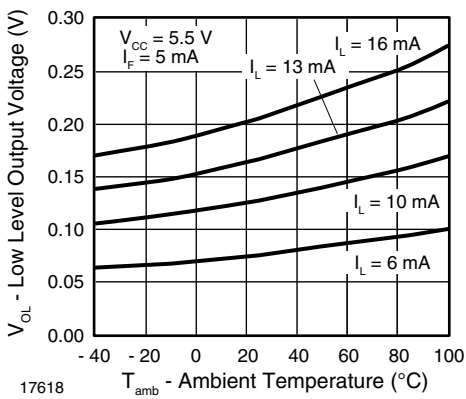


Fig. 10 - Low Level Output Voltage vs. Ambient Temperature



# SFH6755T, SFH6756T, SFH6757T

High Speed Optocoupler, 10 MBd, Vishay Semiconductors  
SOIC-8 Package

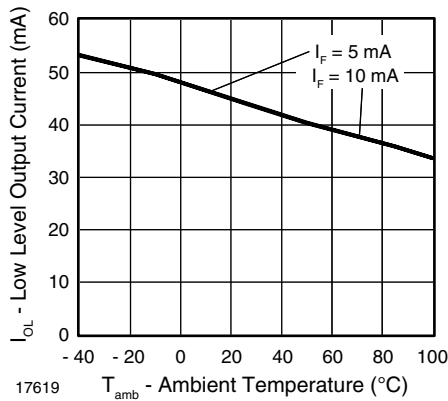


Fig. 11 - Low Level Output Current vs. Ambient Temperature

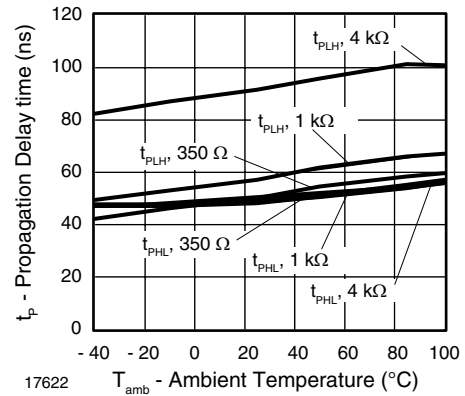


Fig. 14 - Propagation Delay vs. Ambient Temperature

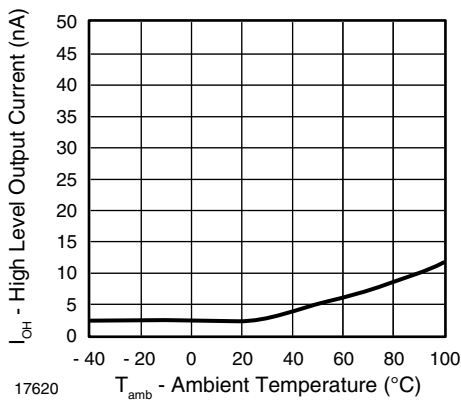


Fig. 12 - High Level Output Current vs. Ambient Temperature

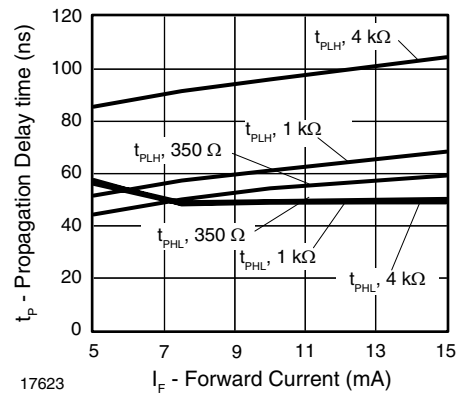


Fig. 15 - Propagation Delay vs. Forward Current

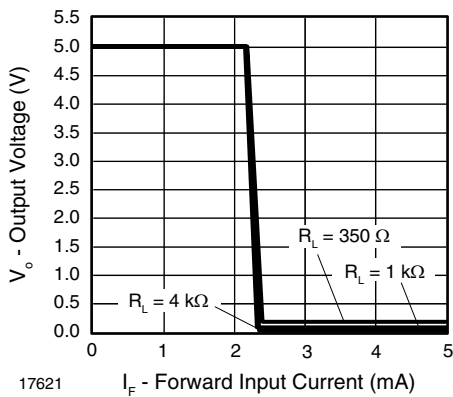


Fig. 13 - Output Voltage vs. Forward Input Current

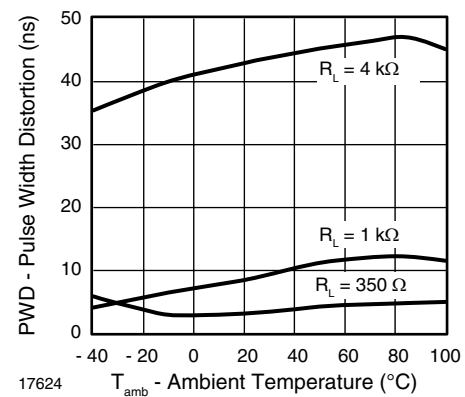


Fig. 16 - Pulse Width Distortion vs. Ambient Temperature

# SFH6755T, SFH6756T, SFH6757T



Vishay Semiconductors High Speed Optocoupler, 10 MBd,  
SOIC-8 Package

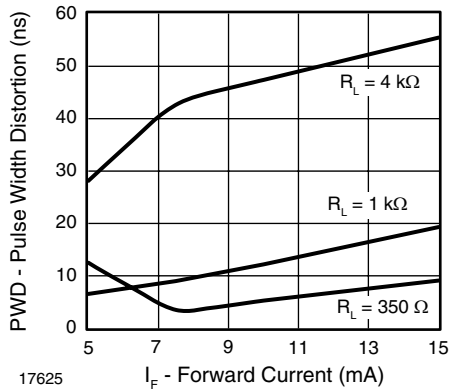


Fig. 17 - Pulse Width Distortion vs. Forward Current

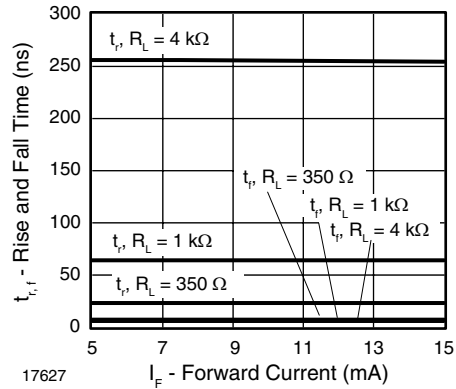


Fig. 19 - Rise and Fall Time vs. Forward Current

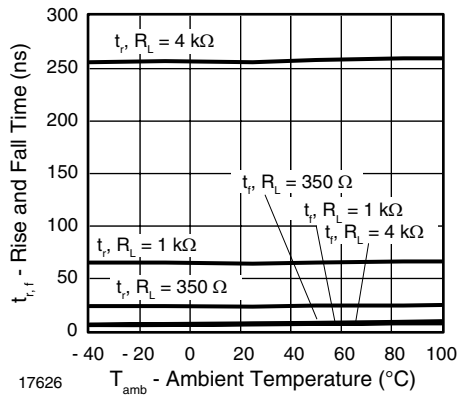
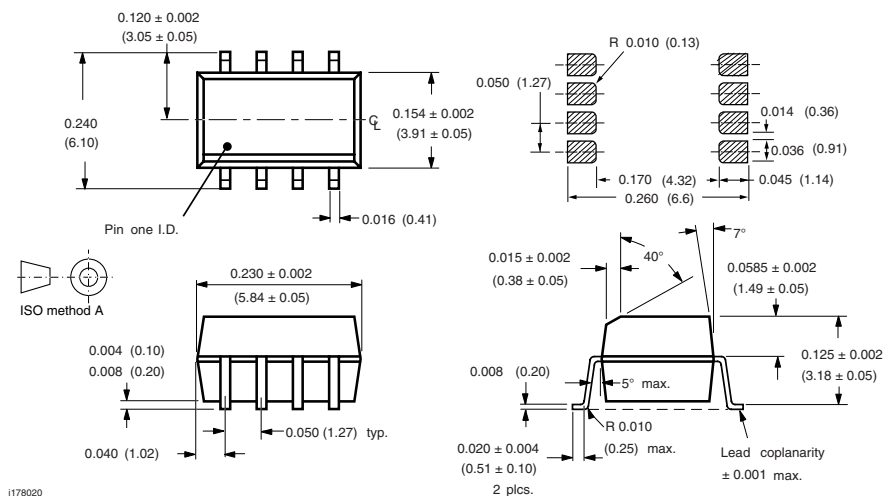


Fig. 18 - Rise and Fall Time vs. Ambient Temperature

## PACKAGE DIMENSIONS in inches (millimeters) DUAL CHANNEL SOIC-8



## ESD CAUTION

This is an ESD (electro static discharge) sensitive device. Electrostatic charges accumulate on the human body and test equipment and can discharge without detection. Therefore, proper ESD precautions are recommended to avoid performance degradation or loss of functionality. ESD withstand voltage of this device is up to 1500 V acc. to JESD22-A114-B.





## OZONE DEPLETING SUBSTANCES POLICY STATEMENT

It is the policy of Vishay Semiconductor GmbH to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively.
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA.
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design  
and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

Vishay Semiconductor GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany



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Наши преимущества:

- Поставка оригинальных импортных электронных компонентов напрямую с производств Америки, Европы и Азии, а так же с крупнейших складов мира;
- Широкая линейка поставок активных и пассивных импортных электронных компонентов (более 30 млн. наименований);
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Помощь Конструкторского Отдела и консультации квалифицированных инженеров;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Поставка электронных компонентов под контролем ВП;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- При необходимости вся продукция военного и аэрокосмического назначения проходит испытания и сертификацию в лаборатории (по согласованию с заказчиком);
- Поставка специализированных компонентов военного и аэрокосмического уровня качества (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Actel, Aeroflex, Peregrine, VPT, Syfer, Eurofarad, Texas Instruments, MS Kennedy, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Компания «Океан Электроники» является официальным дистрибьютором и эксклюзивным представителем в России одного из крупнейших производителей разъемов военного и аэрокосмического назначения «JONHON», а так же официальным дистрибьютором и эксклюзивным представителем в России производителя высокотехнологичных и надежных решений для передачи СВЧ сигналов «FORSTAR».



## JONHON

«JONHON» (основан в 1970 г.)

Разъемы специального, военного и аэрокосмического назначения:

(Применяются в военной, авиационной, аэрокосмической, морской, железнодорожной, горно- и нефтедобывающей отраслях промышленности)

«FORSTAR» (основан в 1998 г.)

ВЧ соединители, коаксиальные кабели, кабельные сборки и микроволновые компоненты:

(Применяются в телекоммуникациях гражданского и специального назначения, в средствах связи, РЛС, а так же военной, авиационной и аэрокосмической отраслях промышленности).



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